

## TOSHIBA MOS DIGITAL INTEGRATED CIRCUIT SILICON GATE CMOS

### 524,288-WORD BY 8-BIT FULL CMOS STATIC RAM

#### DESCRIPTION

The TC55VCM208ASTN is a 4,194,304-bit static random access memory (SRAM) organized as 524,288 words by 8 bits. Fabricated using Toshiba's CMOS Silicon gate process technology, this device operates from a single 2.3 to 3.6 V power supply. Advanced circuit technology provides both high speed and low power at an operating current of 3 mA/MHz and a minimum cycle time of 40 ns. It is automatically placed in low-power mode at 0.7  $\mu$ A standby current (at  $V_{DD} = 3$  V,  $T_a = 25^\circ\text{C}$ , typical) when chip enable ( $\overline{\text{CE1}}$ ) is asserted high or ( $\text{CE2}$ ) is asserted low. There are three control inputs.  $\overline{\text{CE1}}$  and  $\text{CE2}$  are used to select the device and for data retention control, and output enable ( $\overline{\text{OE}}$ ) provides fast memory access. This device is well suited to various microprocessor system applications where high speed, low power and battery backup are required. And, with a guaranteed operating extreme temperature range of  $-40^\circ$  to  $85^\circ\text{C}$ , the TC55VCM208ASTN can be used in environments exhibiting extreme temperature conditions. The TC55VCM208ASTN is available in a plastic 40-pin thin-small outline package (TSOP).

#### FEATURES

- Low-power dissipation  
Operating: 9 mW/MHz (typical)
- Single power supply voltage of 2.3 to 3.6 V
- Power down features using  $\overline{\text{CE1}}$  and  $\text{CE2}$
- Data retention supply voltage of 1.5 to 3.6 V
- Direct TTL compatibility for all inputs and outputs
- Wide operating temperature range of  $-40^\circ$  to  $85^\circ\text{C}$
- Standby Current (maximum):

|       |            |
|-------|------------|
| 3.6 V | 10 $\mu$ A |
| 3.0 V | 5 $\mu$ A  |

- Access Times:

|                                     | TC55VCM208ASTN |       |
|-------------------------------------|----------------|-------|
|                                     | 40             | 55    |
| Access Time                         | 40 ns          | 55 ns |
| $\overline{\text{CE1}}$ Access Time | 40 ns          | 55 ns |
| $\text{CE2}$ Access Time            | 40 ns          | 55 ns |
| $\overline{\text{OE}}$ Access Time  | 25 ns          | 30 ns |

- Package:  
TSOP 40-P-1014-0.50 (Weight:0.30 g typ)

#### PIN ASSIGNMENT (TOP VIEW)

##### 40 PIN TSOP



(Normal)

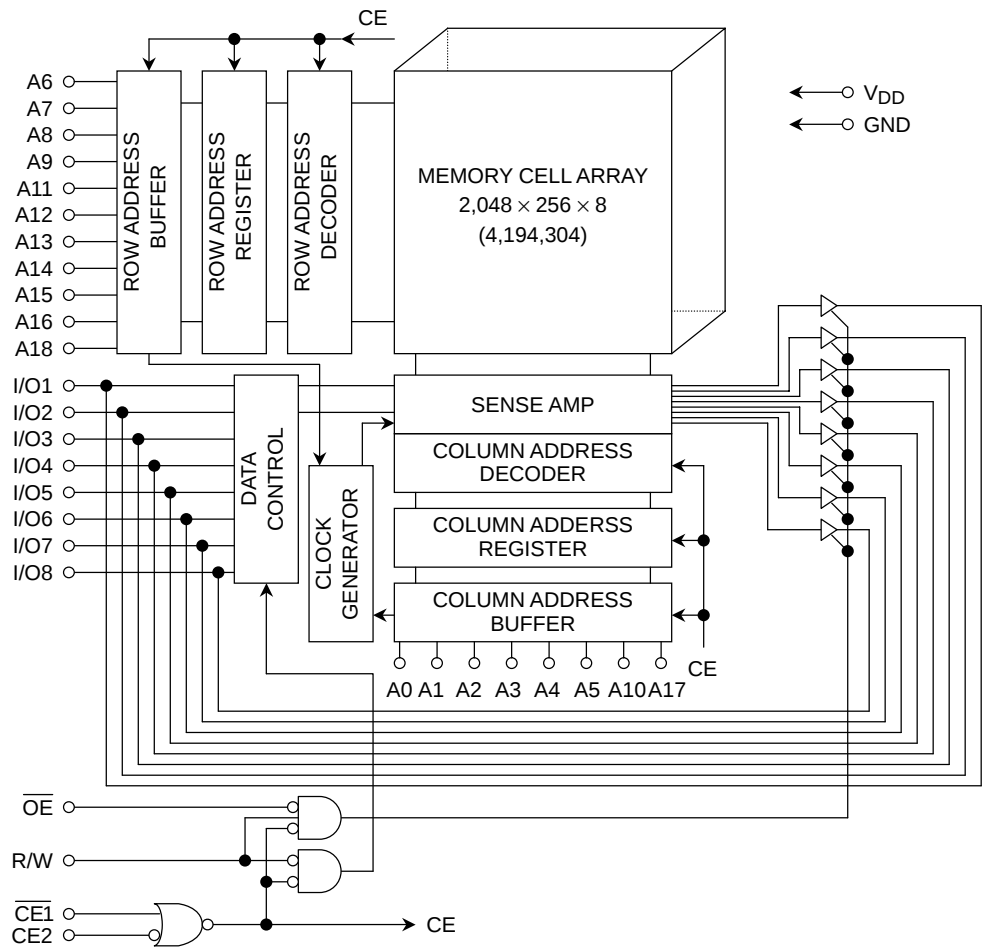
#### PIN NAMES

|                                                 |                     |
|-------------------------------------------------|---------------------|
| A0~A18                                          | Address Inputs      |
| $\overline{\text{CE1}}$ , $\text{CE2}$          | Chip Enable         |
| R/W                                             | Read/Write Control  |
| $\overline{\text{OE}}$                          | Output Enable       |
| $\overline{\text{LB}}$ , $\overline{\text{UB}}$ | Data Byte Control   |
| I/O1~I/O16                                      | Data Inputs/Outputs |
| $V_{DD}$                                        | Power               |
| GND                                             | Ground              |
| NC                                              | No Connection       |
| OP*                                             | Option              |

\*: OP pin must be open or connected to GND.

|          |     |                         |     |                        |      |      |      |      |     |          |          |      |      |      |      |     |    |    |     |     |
|----------|-----|-------------------------|-----|------------------------|------|------|------|------|-----|----------|----------|------|------|------|------|-----|----|----|-----|-----|
| Pin No.  | 1   | 2                       | 3   | 4                      | 5    | 6    | 7    | 8    | 9   | 10       | 11       | 12   | 13   | 14   | 15   | 16  | 17 | 18 | 19  | 20  |
| Pin Name | A16 | A15                     | A14 | A13                    | A12  | A11  | A9   | A8   | R/W | CE2      | OP       | NC   | A18  | A7   | A6   | A5  | A4 | A3 | A2  | A1  |
| Pin No.  | 21  | 22                      | 23  | 24                     | 25   | 26   | 27   | 28   | 29  | 30       | 31       | 32   | 33   | 34   | 35   | 36  | 37 | 38 | 39  | 40  |
| Pin Name | A0  | $\overline{\text{CE1}}$ | GND | $\overline{\text{OE}}$ | I/O1 | I/O2 | I/O3 | I/O4 | NC  | $V_{DD}$ | $V_{DD}$ | I/O5 | I/O6 | I/O7 | I/O8 | A10 | NC | NC | GND | A17 |

BLOCK DIAGRAM



OPERATING MODE

| MODE            | $\overline{CE1}$ | CE2 | $\overline{OE}$ | R/W | I/O1-I/O8 | POWER     |
|-----------------|------------------|-----|-----------------|-----|-----------|-----------|
| Read            | L                | H   | L               | H   | Output    | $I_{DDO}$ |
| Write           | L                | H   | *               | L   | Input     | $I_{DDO}$ |
| Output Deselect | L                | H   | H               | H   | High-Z    | $I_{DDO}$ |
| Standby         | H                | *   | *               | *   | High-Z    | $I_{DDS}$ |
|                 | *                | L   | *               | *   | High-Z    | $I_{DDS}$ |

\* = don't care  
H = logic high  
L = logic low

MAXIMUM RATINGS

| SYMBOL       | RATING                      | VALUE                | UNIT |
|--------------|-----------------------------|----------------------|------|
| $V_{DD}$     | Power Supply Voltage        | -0.3~4.2             | V    |
| $V_{IN}$     | Input Voltage               | -0.3~4.2             | V    |
| $V_{I/O}$    | Input/Output Voltage        | -0.5~ $V_{DD} + 0.5$ | V    |
| $P_D$        | Power Dissipation           | 0.6                  | W    |
| $T_{solder}$ | Soldering Temperature (10s) | 260                  | °C   |
| $T_{stg}$    | Storage Temperature         | -55~150              | °C   |
| $T_{opr}$    | Operating Temperature       | -40~85               | °C   |

\*: -2.0 V when measured at a pulse width of 20ns

**DC RECOMMENDED OPERATING CONDITIONS** ( $T_a = -40^\circ$  to  $85^\circ\text{C}$ )

| SYMBOL   | PARAMETER                     |                                           | MIN      | TYP | MAX                  | UNIT |
|----------|-------------------------------|-------------------------------------------|----------|-----|----------------------|------|
| $V_{DD}$ | Power Supply Voltage          |                                           | 2.3      | —   | 3.6                  | V    |
| $V_{IH}$ | Input High Voltage            | $V_{DD} = 2.3\text{ V} \sim 2.7\text{ V}$ | 2.0      | —   | $V_{DD} + 0.3$       | V    |
|          |                               | $V_{DD} = 2.7\text{ V} \sim 3.6\text{ V}$ | 2.2      |     |                      |      |
| $V_{IL}$ | Input Low Voltage             |                                           | $-0.3^*$ | —   | $V_{DD} \times 0.24$ | V    |
| $V_{DH}$ | Data Retention Supply Voltage |                                           | 1.5      | —   | 3.6                  | V    |

\*:  $-2.0\text{ V}$  when measured at a pulse width of 20ns

**DC CHARACTERISTICS** ( $T_a = -40^\circ$  to  $85^\circ\text{C}$ ,  $V_{DD} = 2.3$  to  $3.6\text{ V}$ )

| SYMBOL            | PARAMETER              | TEST CONDITION                                                                                                                                                    |                                  |                    | MIN  | TYP | MAX  | UNIT |    |
|-------------------|------------------------|-------------------------------------------------------------------------------------------------------------------------------------------------------------------|----------------------------------|--------------------|------|-----|------|------|----|
| I <sub>IL</sub>   | Input Leakage Current  | V <sub>IN</sub> = 0 V~V <sub>DD</sub>                                                                                                                             |                                  |                    | —    | —   | ±1.0 | μA   |    |
| I <sub>OH</sub>   | Output High Current    | V <sub>OH</sub> = V <sub>DD</sub> – 0.5 V                                                                                                                         |                                  |                    | –0.5 | —   | —    | mA   |    |
| I <sub>OL</sub>   | Output Low Current     | V <sub>OL</sub> = 0.4 V                                                                                                                                           |                                  |                    | 2.1  | —   | —    | mA   |    |
| I <sub>LO</sub>   | Output Leakage Current | CE1 = V <sub>IH</sub> or CE2 = V <sub>IL</sub> or R/W = V <sub>IL</sub> or OE = V <sub>IH</sub> ,<br>V <sub>OUT</sub> = 0 V~V <sub>DD</sub>                       |                                  |                    | —    | —   | ±1.0 | μA   |    |
| I <sub>DDO1</sub> | Operating Current      | CE1 = V <sub>IL</sub> and CE2 = V <sub>IH</sub> and<br>R/W = V <sub>IH</sub> , I <sub>OUT</sub> = 0 mA,<br>Other Input = V <sub>IH</sub> /V <sub>IL</sub>         |                                  | t <sub>cycle</sub> | MIN  | —   | —    | 35   | mA |
|                   |                        |                                                                                                                                                                   |                                  |                    | 1 μs | —   | —    | 8    |    |
| I <sub>DDO2</sub> |                        | CE1 = 0.2 V and<br>CE2 = V <sub>DD</sub> – 0.2 V and<br>R/W = V <sub>DD</sub> – 0.2 V,<br>I <sub>OUT</sub> = 0 mA,<br>Other Input = V <sub>DD</sub> – 0.2 V/0.2 V |                                  |                    | MIN  | —   | —    | 30   | mA |
|                   |                        |                                                                                                                                                                   |                                  |                    | 1 μs | —   | —    | 3    |    |
| I <sub>DDS1</sub> | Standby Current        | CE1 = V <sub>IH</sub> or CE2 = V <sub>IL</sub>                                                                                                                    |                                  |                    | —    | —   | 1    | mA   |    |
| I <sub>DDS2</sub> |                        | CE1 = V <sub>DD</sub> – 0.2 V or<br>CE2 = 0.2 V                                                                                                                   | V <sub>DD</sub> =<br>3.3V± 0.3 V | Ta = –40~85°C      | —    | —   | 10   | μA   |    |
|                   |                        |                                                                                                                                                                   | V <sub>DD</sub> =3.0 V           | Ta = 25°C          | —    | 0.7 | —    |      |    |
|                   |                        |                                                                                                                                                                   |                                  | Ta = –40~40°C      | —    | —   | 2    |      |    |
|                   |                        |                                                                                                                                                                   | Ta = –40~85°C                    | —                  | —    | 5   |      |      |    |

**CAPACITANCE** ( $T_a = 25^\circ\text{C}$ ,  $f = 1\text{ MHz}$ )

| SYMBOL    | PARAMETER          | TEST CONDITION         | MAX | UNIT |
|-----------|--------------------|------------------------|-----|------|
| $C_{IN}$  | Input Capacitance  | $V_{IN} = \text{GND}$  | 10  | pF   |
| $C_{OUT}$ | Output Capacitance | $V_{OUT} = \text{GND}$ | 10  | pF   |

Note: This parameter is periodically sampled and is not 100% tested.

## AC CHARACTERISTICS AND OPERATING CONDITIONS

(Ta = -40° to 85°C, V<sub>DD</sub> = 2.7 to 3.6 V)

### READ CYCLE

| SYMBOL           | PARAMETER                                   | TC55VCM208ASTN |     |     |     | UNIT |
|------------------|---------------------------------------------|----------------|-----|-----|-----|------|
|                  |                                             | 40             |     | 55  |     |      |
|                  |                                             | MIN            | MAX | MIN | MAX |      |
| t <sub>RC</sub>  | Read Cycle Time                             | 40             | —   | 55  | —   | ns   |
| t <sub>ACC</sub> | Address Access Time                         | —              | 40  | —   | 55  |      |
| t <sub>CO1</sub> | Chip Enable( $\overline{CE1}$ ) Access Time | —              | 40  | —   | 55  |      |
| t <sub>CO2</sub> | Chip Enable(CE2) Access Time                | —              | 40  | —   | 55  |      |
| t <sub>OE</sub>  | Output Enable Access Time                   | —              | 25  | —   | 30  |      |
| t <sub>COE</sub> | Chip Enable Low to Output Active            | 5              | —   | 5   | —   |      |
| t <sub>OOE</sub> | Output Enable Low to Output Active          | 0              | —   | 0   | —   |      |
| t <sub>OD</sub>  | Chip Enable High to Output High-Z           | —              | 20  | —   | 25  |      |
| t <sub>ODO</sub> | Output Enable High to Output High-Z         | —              | 20  | —   | 25  |      |
| t <sub>OH</sub>  | Output Data Hold Time                       | 10             | —   | 10  | —   |      |

### WRITE CYCLE

| SYMBOL | PARAMETER                   | TC55VCM208ASTN |     |     |     | UNIT |
|--------|-----------------------------|----------------|-----|-----|-----|------|
|        |                             | 40             |     | 55  |     |      |
|        |                             | MIN            | MAX | MIN | MAX |      |
| tWC    | Write Cycle Time            | 40             | —   | 55  | —   | ns   |
| tWP    | Write Pulse Width           | 30             | —   | 40  | —   |      |
| tCW    | Chip Enable to End of Write | 35             | —   | 45  | —   |      |
| tAS    | Address Setup Time          | 0              | —   | 0   | —   |      |
| tWR    | Write Recovery Time         | 0              | —   | 0   | —   |      |
| tODW   | R/W Low to Output High-Z    | —              | 20  | —   | 25  |      |
| tOEW   | R/W High to Output Active   | 0              | —   | 0   | —   |      |
| tDS    | Data Setup Time             | 20             | —   | 25  | —   |      |
| tDH    | Data Hold Time              | 0              | —   | 0   | —   |      |

Note: t<sub>OD</sub>, t<sub>ODO</sub> and t<sub>ODW</sub> are specified in time when an output becomes high impedance, and are not judged depending on an output voltage level.

## AC CHARACTERISTICS AND OPERATING CONDITIONS

(Ta = -40° to 85°C, V<sub>DD</sub> = 2.3 to 3.6 V)

### READ CYCLE

| SYMBOL           | PARAMETER                                   | TC55VCM208ASTN |     |     |     | UNIT |
|------------------|---------------------------------------------|----------------|-----|-----|-----|------|
|                  |                                             | 40             |     | 55  |     |      |
|                  |                                             | MIN            | MAX | MIN | MAX |      |
| t <sub>RC</sub>  | Read Cycle Time                             | 55             | —   | 70  | —   | ns   |
| t <sub>ACC</sub> | Address Access Time                         | —              | 55  | —   | 70  |      |
| t <sub>CO1</sub> | Chip Enable( $\overline{CE1}$ ) Access Time | —              | 55  | —   | 70  |      |
| t <sub>CO2</sub> | Chip Enable(CE2) Access Time                | —              | 55  | —   | 70  |      |
| t <sub>OE</sub>  | Output Enable Access Time                   | —              | 30  | —   | 35  |      |
| t <sub>COE</sub> | Chip Enable Low to Output Active            | 5              | —   | 5   | —   |      |
| t <sub>OOE</sub> | Output Enable Low to Output Active          | 0              | —   | 0   | —   |      |
| t <sub>OD</sub>  | Chip Enable High to Output High-Z           | —              | 25  | —   | 30  |      |
| t <sub>ODO</sub> | Output Enable High to Output High-Z         | —              | 25  | —   | 30  |      |
| t <sub>OH</sub>  | Output Data Hold Time                       | 10             | —   | 10  | —   |      |

### WRITE CYCLE

| SYMBOL           | PARAMETER                   | TC55VCM208ASTN |     |     |     | UNIT |
|------------------|-----------------------------|----------------|-----|-----|-----|------|
|                  |                             | 40             |     | 55  |     |      |
|                  |                             | MIN            | MAX | MIN | MAX |      |
| t <sub>WC</sub>  | Write Cycle Time            | 55             | —   | 70  | —   | ns   |
| t <sub>WP</sub>  | Write Pulse Width           | 40             | —   | 50  | —   |      |
| t <sub>CW</sub>  | Chip Enable to End of Write | 45             | —   | 55  | —   |      |
| t <sub>AS</sub>  | Address Setup Time          | 0              | —   | 0   | —   |      |
| t <sub>WR</sub>  | Write Recovery Time         | 0              | —   | 0   | —   |      |
| t <sub>ODW</sub> | R/W Low to Output High-Z    | —              | 25  | —   | 30  |      |
| t <sub>OEW</sub> | R/W High to Output Active   | 0              | —   | 0   | —   |      |
| t <sub>DS</sub>  | Data Setup Time             | 25             | —   | 30  | —   |      |
| t <sub>DH</sub>  | Data Hold Time              | 0              | —   | 0   | —   |      |

Note: t<sub>OD</sub>, t<sub>ODO</sub> and t<sub>ODW</sub> are specified in time when an output becomes high impedance, and are not judged depending on an output voltage level.

AC TEST CONDITIONS

| PARAMETER           | TEST CONDITION                                       |
|---------------------|------------------------------------------------------|
| Input pulse level   | 0.2 V, $V_{DD} \times 0.7 \text{ V} + 0.2 \text{ V}$ |
| $t_R$ , $t_F$       | 1V / ns(Fig.1)                                       |
| Timing measurements | $V_{DD} \times 0.5$                                  |
| Reference level     | $V_{DD} \times 0.5$                                  |
| Output load         | 30 pF + 1 TTL Gate(Fig.2)                            |

Fig.1 : Input rise and fall time

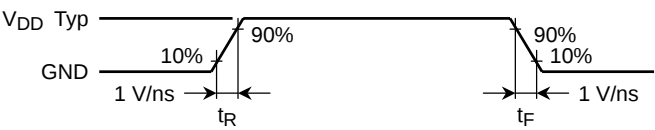
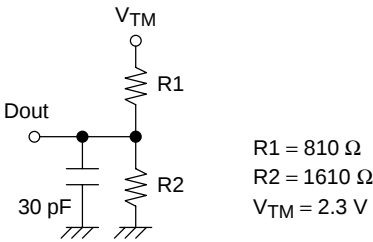
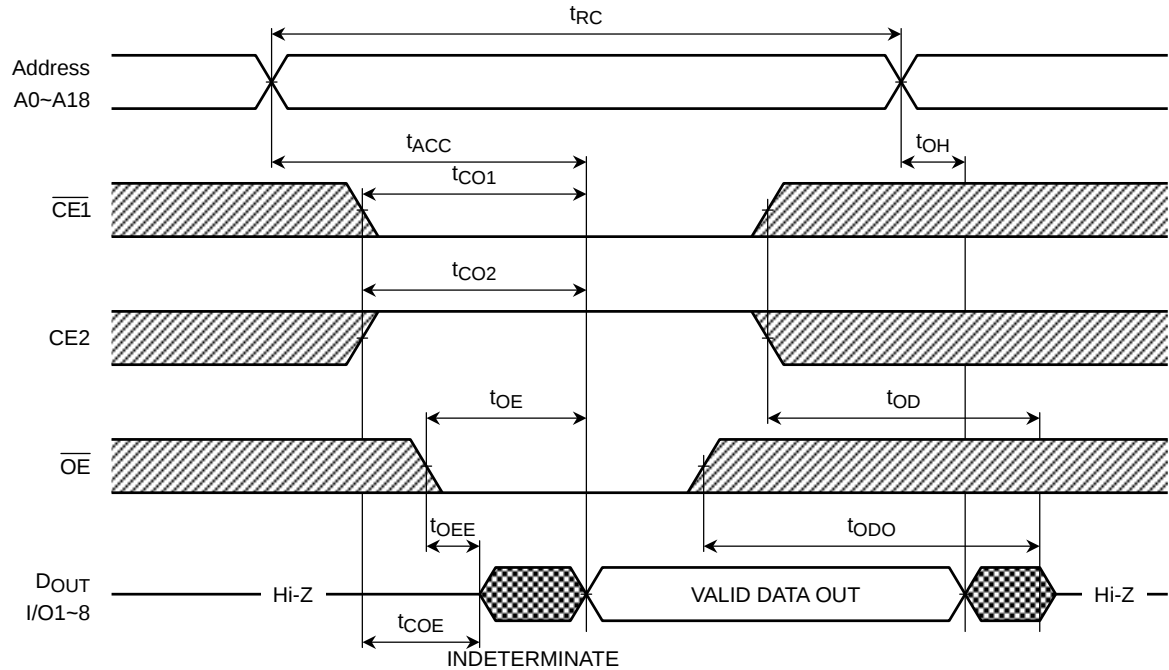


Fig.2 : Output load

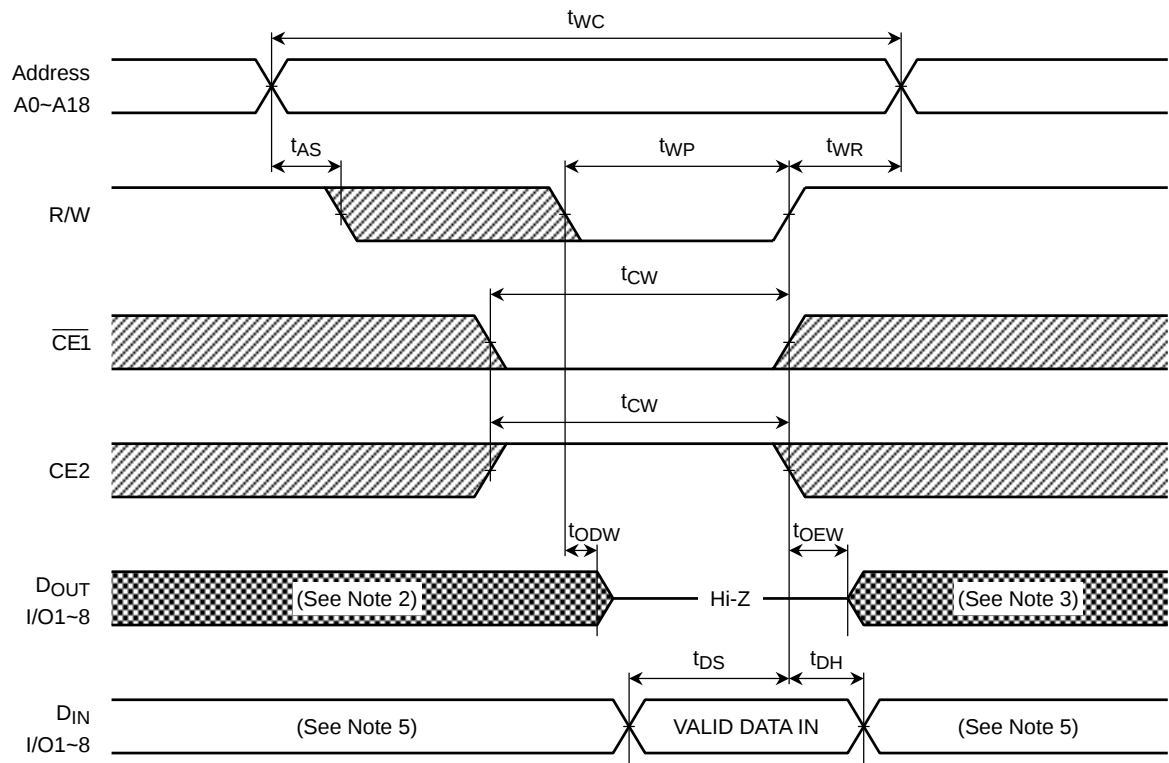


**TIMING DIAGRAMS**

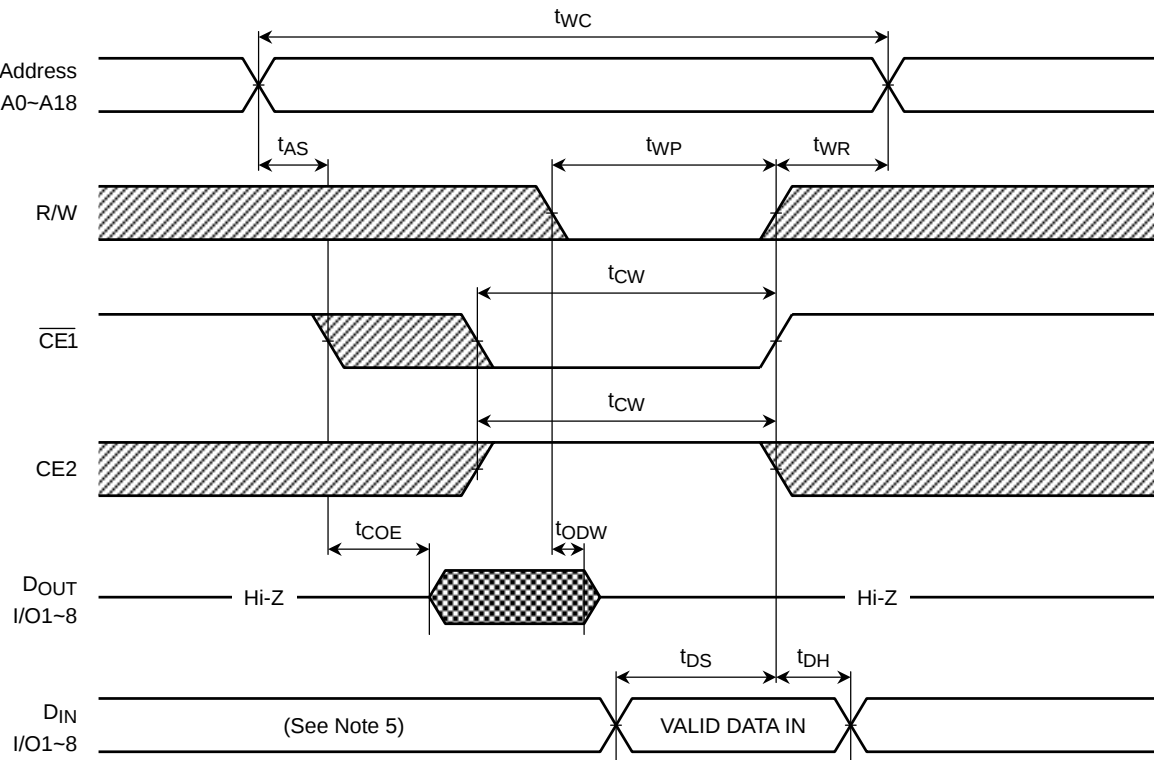
**READ CYCLE** (See Note 1)



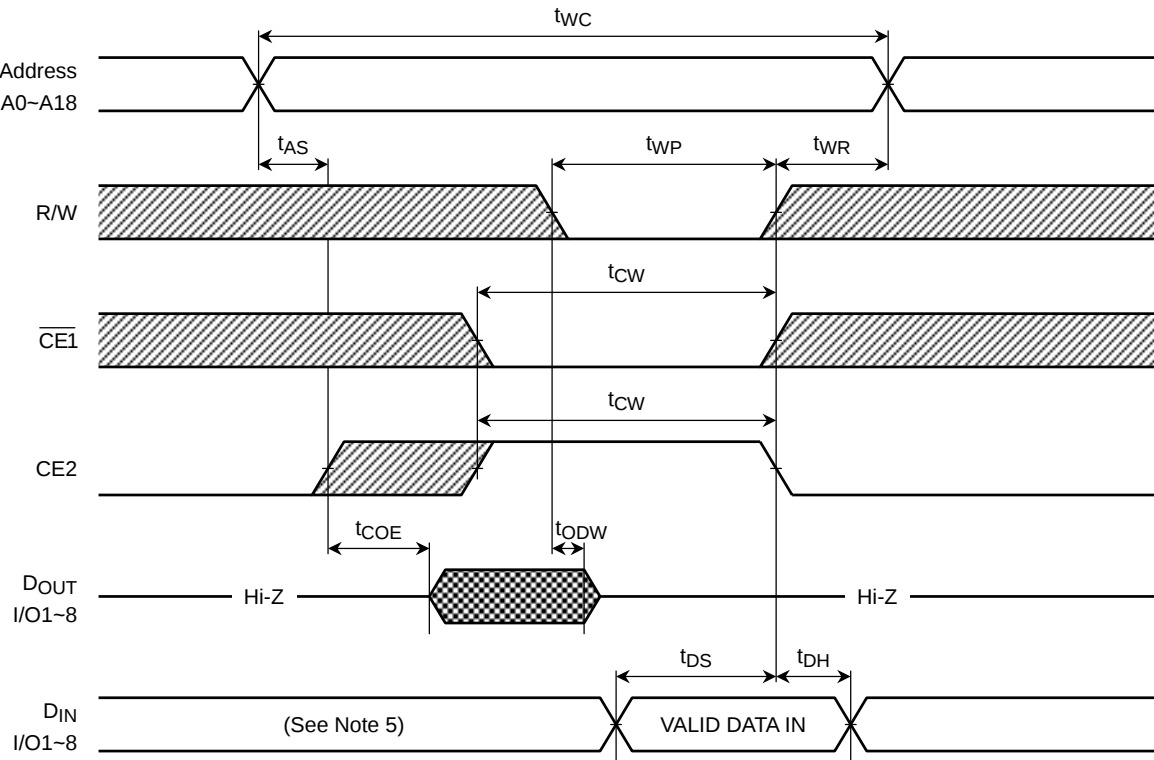
**WRITE CYCLE 1 (R/W CONTROLLED)** (See Note 4)



WRITE CYCLE 2 ( $\overline{\text{CE1}}$  CONTROLLED) (See Note 4)



WRITE CYCLE 3 (CE2 CONTROLLED) (See Note 4)



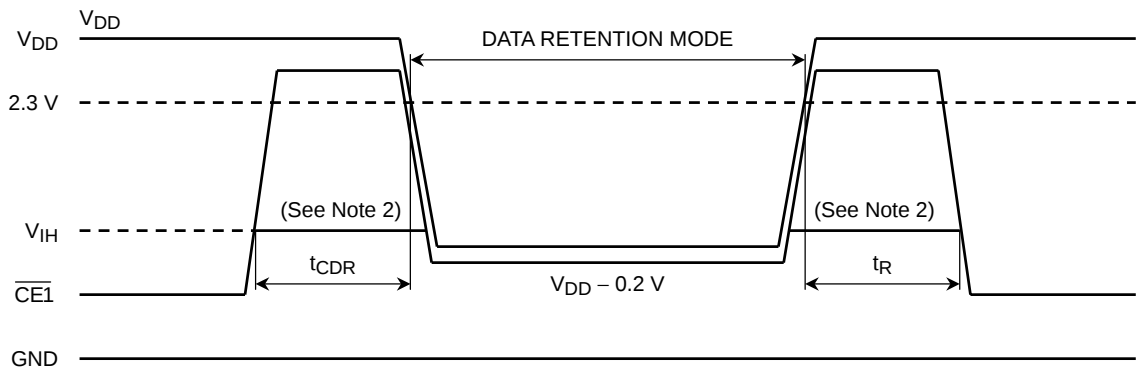
Note:

- (1) R/W remains HIGH for the read cycle.
- (2) If  $\overline{\text{CE1}}$  goes LOW(or CE2 goes HIGH) coincident with or after R/W goes LOW, the outputs will remain at high impedance.
- (3) If  $\overline{\text{CE1}}$  goes HIGH(or CE2 goes LOW) coincident with or before R/W goes HIGH, the outputs will remain at high impedance.
- (4) If  $\overline{\text{OE}}$  is HIGH during the write cycle, the outputs will remain at high impedance.
- (5) Because I/O signals may be in the output state at this time, input signals of reverse polarity must not be applied.

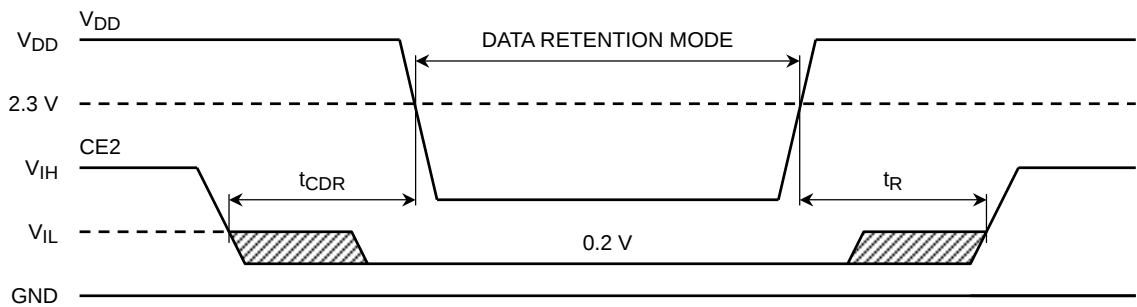
DATA RETENTION CHARACTERISTICS (Ta = -40° to 85°C)

| SYMBOL            | PARAMETER                                 |                                       | MIN | TYP | MAX | UNIT |
|-------------------|-------------------------------------------|---------------------------------------|-----|-----|-----|------|
| V <sub>DH</sub>   | Data Retention Supply Voltage             |                                       | 1.5 | —   | 3.6 | V    |
| I <sub>DDS2</sub> | Standby Current                           | V <sub>DH</sub> = 3.6 V Ta = -40~85°C | —   | —   | 10  | μA   |
|                   |                                           | V <sub>DH</sub> = 3.0 V Ta = -40~40°C | —   | —   | 2   |      |
|                   |                                           | V <sub>DH</sub> = 3.0 V Ta = -40~85°C | —   | —   | 5   |      |
| t <sub>CDR</sub>  | Chip Deselect to Data Retention Mode Time |                                       | 0   | —   | —   | ns   |
| t <sub>R</sub>    | Recovery Time                             |                                       | 5   | —   | —   | ms   |

$\overline{\text{CE1}}$  CONTROLLED DATA RETENTION MODE (See Note 1)



CE2 CONTROLLED DATA RETENTION MODE (See Note 3)



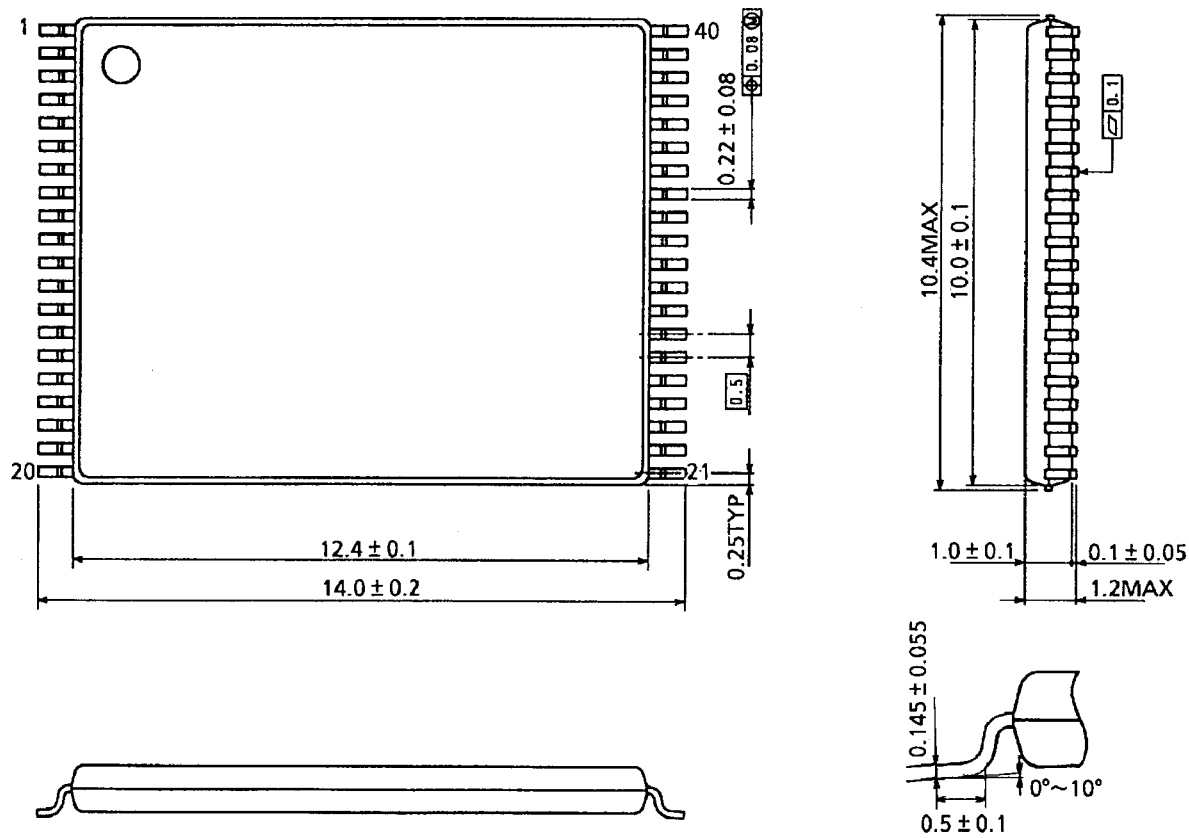
Note:

- (1) In  $\overline{\text{CE1}}$  controlled data retention mode, minimum standby current mode is entered when  $\text{CE2} \leq 0.2 \text{ V}$  or  $\text{CE2} \geq \text{V}_{\text{DD}} - 0.2 \text{ V}$ .
- (2) When  $\overline{\text{CE1}}$  is operating at the  $\text{V}_{\text{IH}}(\text{min.})$  level, the operating current is given by  $\text{I}_{\text{DDS1}}$  during the transition of  $\text{V}_{\text{DD}}$  from 2.3(2.7) to 2.2V(2.4 V).
- (3) In  $\text{CE2}$  controlled data retention mode, minimum standby current mode is entered when  $\text{CE2} \leq 0.2 \text{ V}$ .

PACKAGE DIMENSIONS

TSOP I 40-P-1014-0.50

Unit : mm



Weight:0.30 g (typ)

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